CHINA BASE INTERNATIONAL

SOT-89

PBSS5320U

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PNP Silicon Epitaxial Planar Transistor

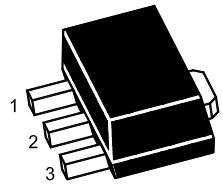
Features

Low $V_{CE(sat)}$, high current.

Applications

General purpose switching and muting, LCD back-lighting, supply line switching circuits.

MARKING:5320



1.Base 2.Collector 3.Emitter

SOT-89 Plastic Package

Absolute Maximum Ratings(Ta=25℃)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-20	V
Collector to Emitter Voltage	V_{CEO}	-20	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-2.0	A
Peak Collector Current	I_{CM}	-5.0	A
Base Current	I_B	-0.5	A
total power dissipation	$P_{tot(1)}$ 注2	600	mW
total power dissipation	$P_{tot(2)}$ 注1、2	1.2	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55～150	℃

Electrical Characteristics(Ta=25℃)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	V_{CB}=-20V I_E=0			-0.1	μA
		V_{CB}=-20V I_E=0 T_j=150℃			-50	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-5.0V I_C=0			-0.1	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=-2.0V I_C=-500mA	220		450	
	$h_{FE(2)}$	V_{CE}=-2.0V I_C=-100mA	220			
	$h_{FE(3)}$	V_{CE}=-2.0V I_C=-1.0A	200			
	$h_{FE(4)}$	V_{CE}=-2.0V I_C=-2.0A	150			
	$h_{FE(5)}$	V_{CE}=-2.0V I_C=-3.0A	100			
Collector-Emitter Saturation Voltage	$V_{CE(sat)(1)}$	I_C=-500mA I_B=-50mA			-100	mV
	$V_{CE(sat)(2)}$	I_C=-2.0A I_B=-100mA			-300	mV
Equivalent on-resistance	$R_{CE(sat)}$	I_C=-2.0A I_B=-200mA		125	150	mΩ
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=-2.0A I_B=-100mA			-1.1	V
		I_C=-3.0A I_B=-300mA			-1.2	V
Base-Emitter Voltage	$V_{BE(ON)}$	V_{CE}=-2.0V I_C=-1.0A			-1.2	V
Transition Frequency	f_T	V_{CE}=-5.0V I_C=-100mA f=100MHz	100			MHz
Collector Capacitance	C_C	V_{CB}=-10V I_E=0 f=1.0MHz			50	pF

Electrical Characteristic Curve